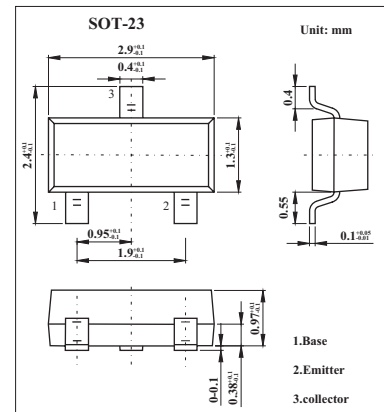


Medium Power Transistor

2SD1484K

■ Features

- High current.($I_c=5A$).
- Low saturation voltage, typically $V_{CE(sat)}=0.1V$ at $I_c / I_B=150mA / 15mA$.



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	50	V
Collector-emitter voltage	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	5	V
Collector current *	I_c	0.5	A
Collector power dissipation	P_c	0.2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CB0}	$I_c=100\mu A$	50			V
Collector-emitter breakdown voltage	BV_{CE0}	$I_c=1mA$	50			V
Emitter-base breakdown voltage	BV_{EB0}	$I_E=100\mu A$	5			V
Collector cutoff current	I_{cB0}	$V_{CB}=30V$			0.5	μA
Emitter cutoff current	I_{EB0}	$V_{EB}=4V$			0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c/I_B=150mA/15mA$			0.4	V
DC current transfer ratio	h_{FE}	$V_{CE}=3V, I_c=0.01A$	120		390	
Output capacitance	f_T	$V_{CE}=5V, I_E=-20mA, f=100MHz$		250		MHz
Transition frequency	C_{ob}	$V_{CB}=10V, I_E=0A, f=1MHz$		6.5		pF

■ hFE Classification

Marking	YQ	YR
hFE	120~270	180~390